FEATURES:

- 0.5 MICRON CMOS Technology
- Typical tSK(o) (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- Vcc = 3.3V ± 0.3V, Normal Range
- Vcc = 2.7V to 3.6V, Extended Range
- $VCC = 2.5V \pm 0.2V$
- CMOS power levels (0.4 µ W typ. static)
- · Rail-to-Rail output swing for increased noise margin
- · Available in TSSOP package

DRIVE FEATURES:

- High Output Drivers: ±24mA
- · Suitable for heavy loads

DESCRIPTION:

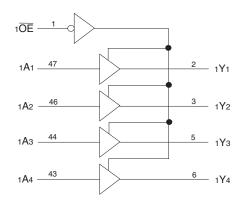
This 16-bit buffer/driver is built using advanced dual metal CMOS technology. The ALVC16244A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable (\overline{OE}) inputs.

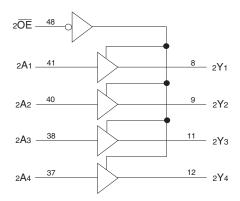
The ALVC16244A has been designed with a ± 24 mA output driver. This driver is capable of driving a moderate to heavy load while maintaining speed performance.

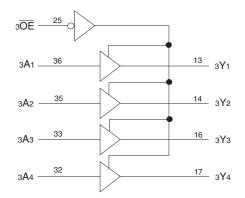
APPLICATIONS:

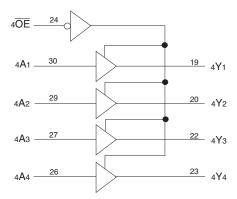
- 3.3V high speed systems
- · 3.3V and lower voltage computing systems

FUNCTIONAL BLOCK DIAGRAM







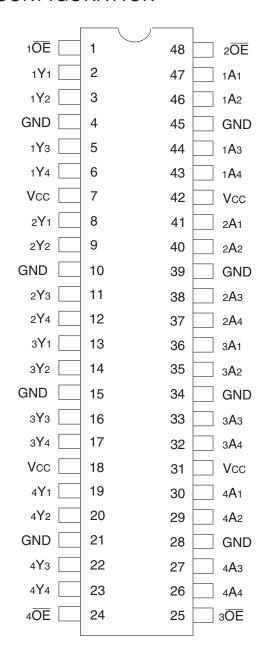


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INDUSTRIAL TEMPERATURE RANGE

JUNE 2016

PIN CONFIGURATION



TSSOP TOP VIEW

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	٧
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
Tstg	Storage Temperature	-65 to +150	°C
Іоит	DC Output Current	-50 to +50	mA
lıĸ	Continuous Clamp Current, VI < 0 or VI > VCC	±50	mA
Іок	Continuous Clamp Current, Vo < 0	-50	mA
lcc Iss	Continuous Current through each Vcc or GND	±100	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. Vcc terminals.
- 3. All terminals except Vcc.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Тур.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	5	7	рF
Соит	Output Capacitance	Vout = 0V	7	9	рF
Соит	I/O Port Capacitance	VIN = 0V	7	9	pF

NOTE:

1. As applicable to the device type.

PIN DESCRIPTION

Pin Names	Description		
xŌĒ	3-State Output Enable Inputs (Active LOW)		
xAx	Data Inputs		
хҮх	3-State Outputs		

FUNCTION TABLE(1)

Inp	Outputs	
×ŌĒ	xAx	xYx
L	Н	Н
L	L	L
Н	Х	Z

NOTE:

1. H = HIGH Voltage Level

X = Don't Care

L = LOW Voltage Level

Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: TA = -40°C to +85°C

Symbol	Parameter	Test Co	nditions	Min.	Typ. ⁽¹⁾	Max.	Unit
VIH	Input HIGH Voltage Level	Vcc = 2.3V to 2.7V		1.7	_	_	V
		Vcc = 2.7V to 3.6V		2	_	_]
VIL	Input LOW Voltage Level	Vcc = 2.3V to 2.7V			_	0.7	V
		Vcc = 2.7V to 3.6V		_	_	0.8	
Іін	Input HIGH Current	Vcc = 3.6V	VI = VCC	_	_	±5	μA
lıL	Input LOW Current	Vcc = 3.6V	Vı = GND	_	_	±5	μA
lozh	High Impedance Output Current	Vcc = 3.6V	Vo = Vcc	_	_	±10	μA
lozl	(3-State Output pins)		Vo = GND	_	_	±10	
Vik	Clamp Diode Voltage	Vcc = 2.3V, IIN = -18mA		_	-0.7	-1.2	V
VH	Input Hysteresis	Vcc = 3.3V			100	_	mV
ICCL ICCH ICCZ	Quiescent Power Supply Current	Vcc = 3.6V Vin = GND or Vcc		_	0.1	40	μΑ
Δlcc	Quiescent Power Supply Current Variation	One input at Vcc - 0.6V, other	inputs at Vcc or GND	_	_	750	μΑ

NOTE:

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Max.	Unit
Voh	Output HIGH Voltage	Vcc = 2.3V to 3.6V	Iон = - 0.1mA	Vcc-0.2	_	V
		Vcc = 2.3V	Ioн= -6mA	2		
		Vcc = 2.3V	IOH = - 12mA	1.7	_	
		Vcc = 2.7V		2.2	_	
		Vcc = 3V		2.4	_	
		Vcc = 3V	Iон = - 24mA	2	_	
Vol	Output LOW Voltage	Vcc = 2.3V to 3.6V	IOL = 0.1mA	_	0.2	V
		Vcc = 2.3V	IoL = 6mA	_	0.4	
			IoL = 12mA	_	0.7	
		Vcc = 2.7V	IoL = 12mA	_	0.4	
		Vcc = 3V	IoL = 24mA	_	0.55	

NOTE:

^{1.} Typical values are at Vcc = 3.3V, +25°C ambient.

^{1.} VIH and VIL must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate Vcc range. TA = - 40°C to + 85°C.

OPERATING CHARACTERISTICS, TA = 25°C

			$Vcc = 2.5V \pm 0.2V$	$VCC = 3.3V \pm 0.3V$	
Symbol	Parameter	Test Conditions	Typical	Typical	Unit
CPD	Power Dissipation Capacitance Outputs enabled	CL = 0pF, f = 10Mhz	16	19	pF
CPD	Power Dissipation Capacitance Outputs disabled		4	5	

SWITCHING CHARACTERISTICS(1)

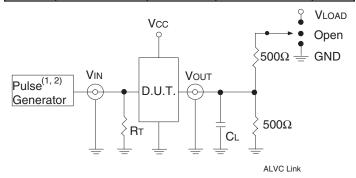
		Vcc = 2.	5V ± 0.2V	Vcc	= 2.7V	Vcc = 3.3	V ± 0.3V	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t PLH	Propagation Delay	1	4.4	_	4	1	3.6	ns
tpHL	xA to xBx							
tpzh	Output Enable Time	1	6.3	_	6	1	5	ns
tPZL	OE to xBx							
tpHZ	Output Disable Time	1	5.8	_	5.2	1	5	ns
tPLZ	OE to xBx							
tsk(o)	Output Skew ⁽²⁾	_	_	_	_	_	500	ps

NOTES:

- 1. See TEST CIRCUITS AND WAVEFORMS. $TA = -40^{\circ}C$ to + 85°C.
- 2. Skew between any two outputs of the same package and switching in the same direction.

TEST CIRCUITS AND WAVEFORMS TEST CONDITIONS

Symbol	Vcc ⁽¹⁾ =3.3V±0.3V	Vcc ⁽¹⁾ =2.7V	Vcc ⁽²⁾ =2.5V±0.2V	Unit
VLOAD	6	6	2 x Vcc	V
VIH	2.7	2.7	Vcc	V
VT	1.5	1.5	Vcc/2	V
VLZ	300	300	150	mV
VHZ	300	300	150	mV
CL	50	50	30	pF



Test Circuit for All Outputs

DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

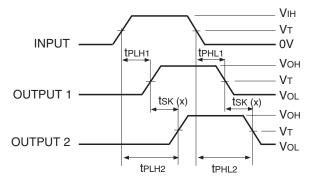
RT = Termination resistance: should be equal to ZouT of the Pulse Generator.

NOTES:

- 1. Pulse Generator for All Pulses: Rate \leq 1.0MHz; tF \leq 2.5ns; tR \leq 2.5ns.
- 2. Pulse Generator for All Pulses: Rate \leq 1.0MHz; tF \leq 2ns; tR \leq 2ns.

SWITCH POSITION

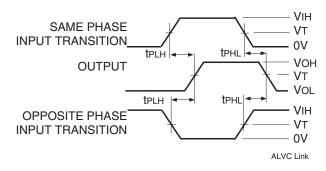
Test	Switch
Open Drain Disable Low Enable Low	VLOAD
Disable High Enable High	GND
All Other Tests	Open



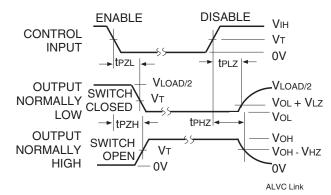
tsk(x) = |tPLH2 - tPLH1| or tPHL2 - tPHL1|Output Skew - tsk(x)ALVC Link

NOTES:

- 1. For tsk(o) OUTPUT1 and OUTPUT2 are any two outputs.
- 2. For tsk(b) OUTPUT1 and OUTPUT2 are in the same bank.



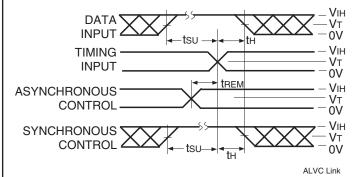
Propagation Delay



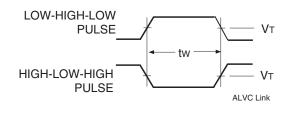
Enable and Disable Times

NOTE:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

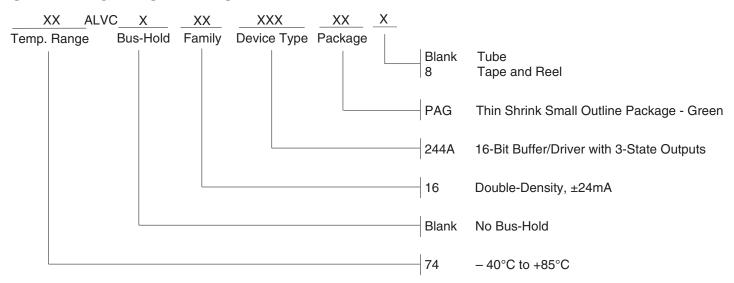


Set-up, Hold, and Release Times



Pulse Width

ORDERING INFORMATION



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Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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